

Product Overview

FCP260N65S3: Power MOSFET, N-Channel, SUPERFET® III, Easy Drive, 650 V, 12 A, 260 mΩ , TO-220

For complete documentation, see the data sheet.

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

Features

- 700 V @ T_J = 150 °C
- Low Effective Output Capacitance (Typ. C_{oss}(eff.) = 248 pF)
- Ultra Low Gate Charge (Typ. Q_g = 24 nC)
- Optimized Capacitance
- Internal Gate resistance: 8.7ohm
- Typ. R_{DS(on)} = 222 mΩ
- 100% Avalanche Tested
- RoHS Compliant

Applications

- Computing
- Consumer
- Industrial

Benefits

- Higher system reliability at low temperature operation
- Lower switching loss
- Lower switching loss
- Lower peak V_{ds} and lower V_{gs} oscillation
- Lower peak V_{ds} and lower V_{gs} oscillation

End Products

- Notebook / Desktop computer / Game console
- Telecom / Server
- LCD / LED TV
- LED Lighting / Ballast
- Adapter

Part Electrical Specifications

Product	Compliance	Status	Chan- nel Polar- ity	Confi- gura- tion	V _{BRD} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Pack- age Type
FCP260N65S3	Pb-free Halide free	Active	N- Chan- nel	Singl- e	650	±30	4.5	12	90	-	-	260	-	24	1010	TO- 220-3

For more information please contact your local sales support at www.onsemi.com.

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